

■ **FEATURES**

- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

■ **TYPICAL APPLICATIONS**

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

■ **MECHANICAL DATA**

- **Package:** ITO-220AC  
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked

■ **MAXIMUM RATINGS** ( $T_a=25^{\circ}\text{C}$  Unless otherwise specified )

PARAMETER	SYMBOL	UNIT	MUR820F
Device marking code			MUR820F
Repetitive Peak Reverse Voltage	$V_{RRM}$	V	200
Average Rectified Output Current @60Hz sine wave, R-load, $T_c$ (FIG.1)	$I_o$	A	8
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, $T_j=25^{\circ}\text{C}$	$I_{FSM}$	A	100
Current Squared Time @1ms $\leq t \leq$ 8.3ms $T_j=25^{\circ}\text{C}$	$I^2t$	A <sup>2</sup> s	41
Storage Temperature	$T_{slg}$	$^{\circ}\text{C}$	-55 ~ +175
Junction Temperature	$T_j$	$^{\circ}\text{C}$	-55 ~ +175
Typical Junction capacitance @4V,1MHz	$C_j$	pF	70
Mounting torque @recommend torque: 5kg·cm	Tor	kg·cm	8

■ **THERMAL CHARACTERISTICS** ( $T_a=25^{\circ}\text{C}$  Unless otherwise specified )

PARAMETER	SYMBOL	UNIT	MUR820F	
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	$^{\circ}\text{C/W}$	4.0
	Between junction and Air	$R_{\theta J-A}$	$^{\circ}\text{C/W}$	50

■ **PACKAGING INFORMATION**

PREFERRED P/N	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MUR820F	Approximate 1.6	50	1000	5000	Tube

### ■ ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max	
Instantaneous forward voltage drop per diode	V <sub>FM</sub>	V	I <sub>FM</sub> =8.0A @T <sub>j</sub> =25°C	-	0.90	1.0	
			I <sub>FM</sub> =8.0A @T <sub>j</sub> =150°C	-	0.78	0.9	
DC reverse current at rated DC blocking voltage per diode	I <sub>RRM1</sub>	uA	V <sub>RM</sub> =V <sub>RRM</sub> T <sub>j</sub> =25°C	-	-	5	
	I <sub>RRM2</sub>		V <sub>RM</sub> =V <sub>RRM</sub> T <sub>j</sub> =150°C	-	20	50	
Reverse Recovery Time	T <sub>RR</sub>	ns	I <sub>F</sub> =0.5A I <sub>RM</sub> =1A I <sub>RR</sub> =0.25A T <sub>j</sub> =25°C	-	25	35	
			T <sub>j</sub> =25°C	-	20	-	
			T <sub>j</sub> =125°C	-	35	-	
Peak recovery current	I <sub>RRM</sub>	A	T <sub>j</sub> =25°C	-	3.7	-	
			T <sub>j</sub> =125°C	-	6.4	-	
Reverse recovery charge	Q <sub>rr</sub>	nC	T <sub>j</sub> =25°C	I <sub>F</sub> =8A di/dt=-200A/us V <sub>RM</sub> =100V	-	34	-
			T <sub>j</sub> =125°C		-	115	-

### ■ CHARACTERISTICS (TYPICAL)

FIG1: I<sub>o</sub> -T<sub>c</sub> Curve

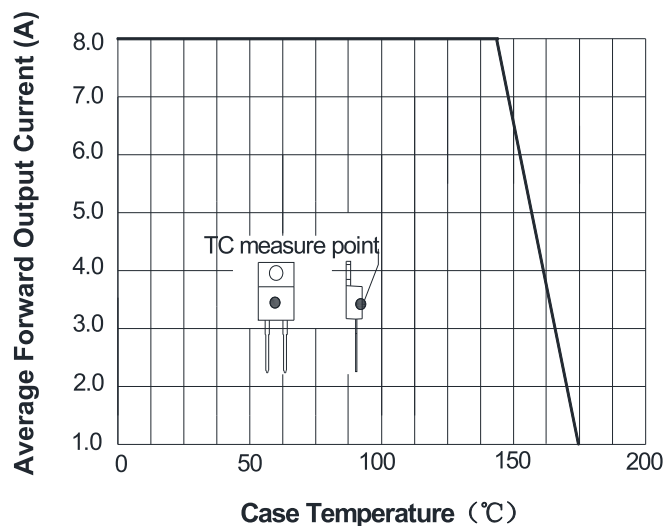


FIG2: Surge Forward Current Capability

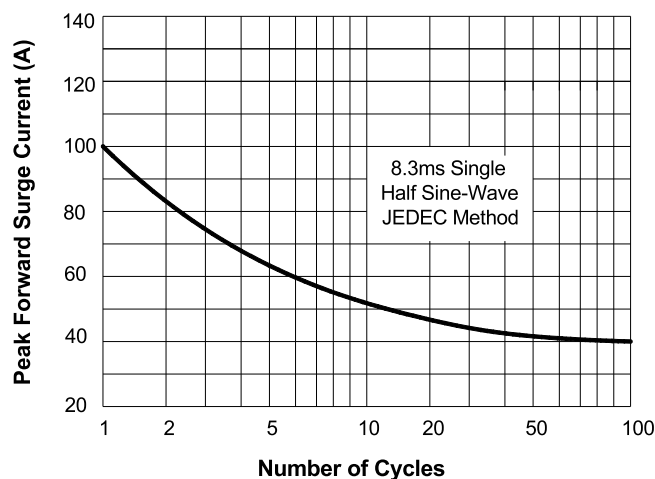


FIG3: Forward Voltage

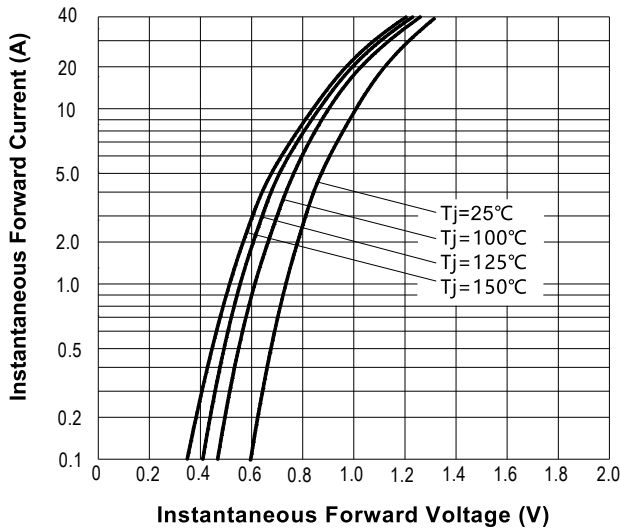


FIG.4: Instantaneous Reverse Characteristics

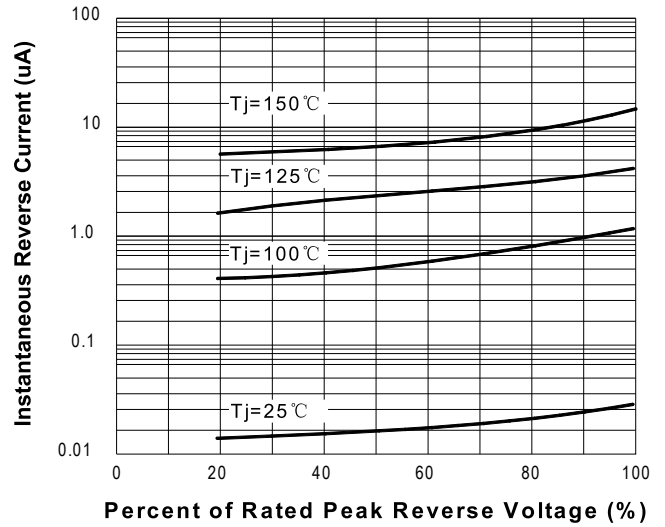
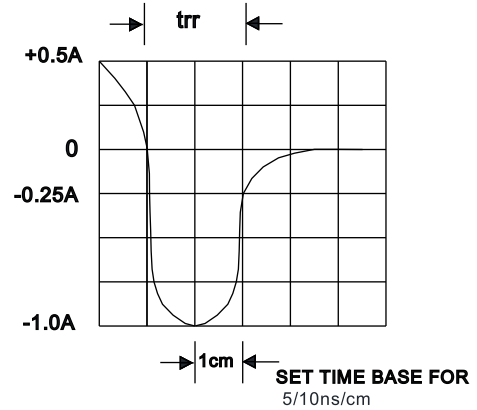
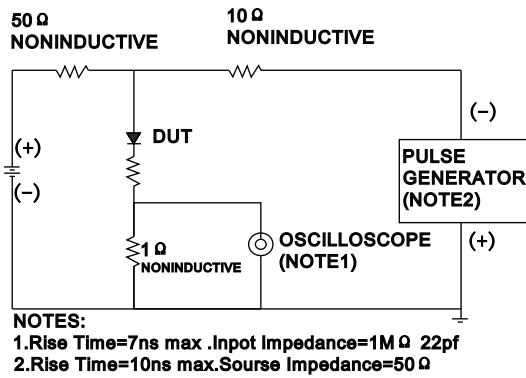
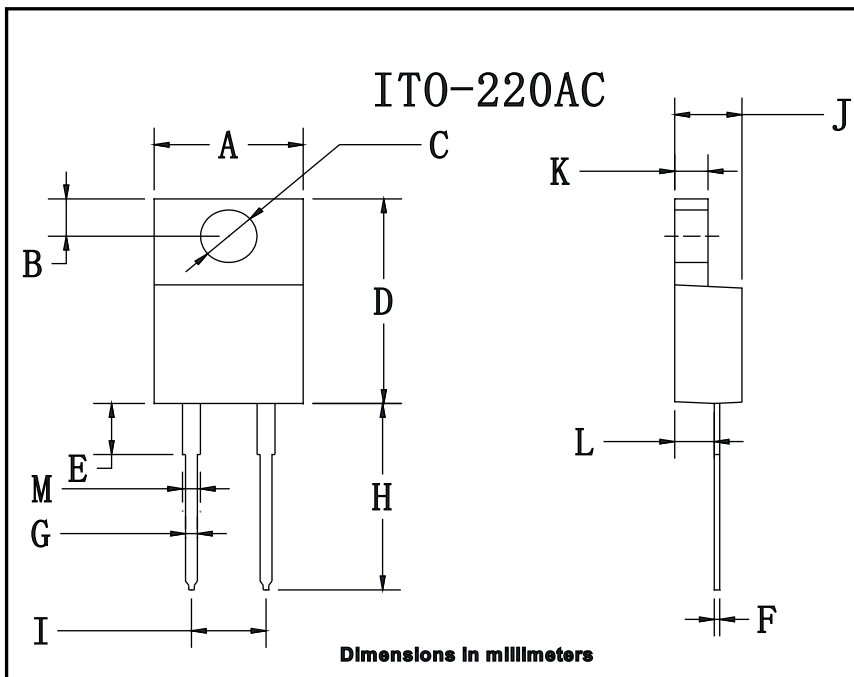


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



■ **OUTLINE DIMENSIONS**



ITO-220AC		
Dim	Min	Max
A	9.8	10.2
B	2.25	2.75
C	2.95	3.45
D	14.75	15.25
E	3.5	4.1
F	0.45	0.75
G	0.45	0.75
H	13.35	14.15
I	4.97	5.23
J	4.3	4.8
K	2.5	2.74
L	2.58	2.82
M	1.03	1.43